

In the Drawings:

Please replace Figs. 1 –21 with the enclosed Replacement sheets of formal drawings.

Fig. 1

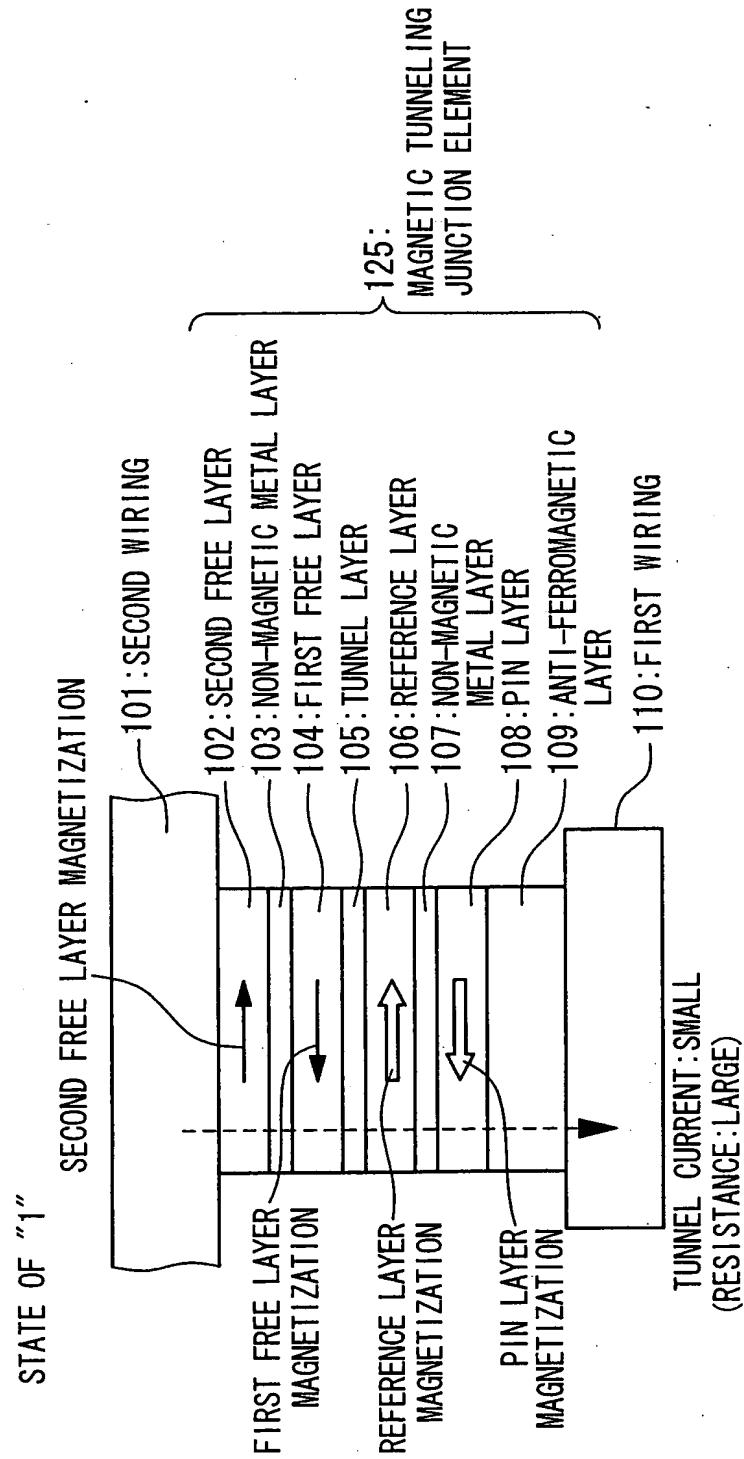


Fig. 2

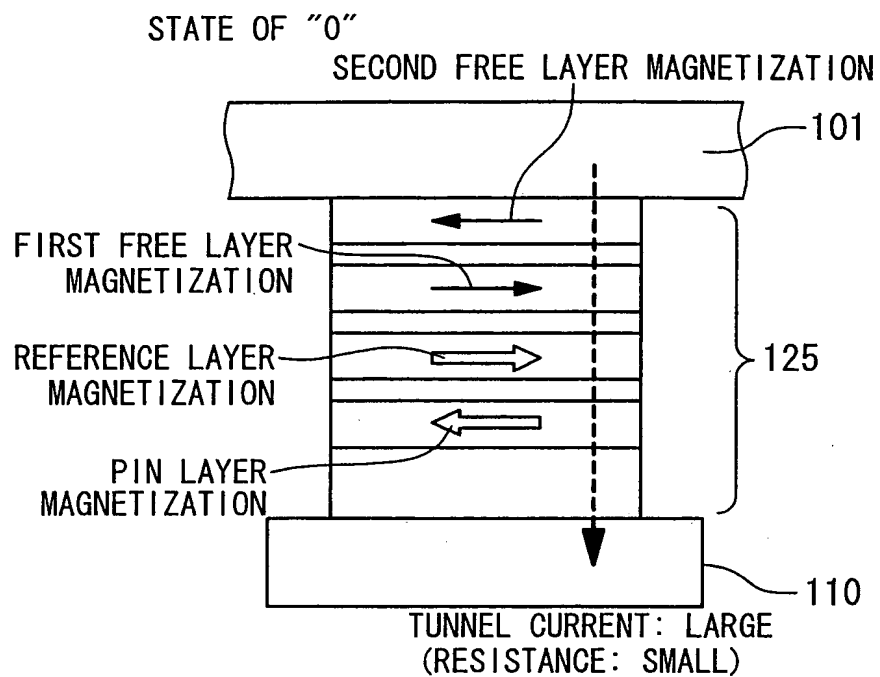


Fig. 3

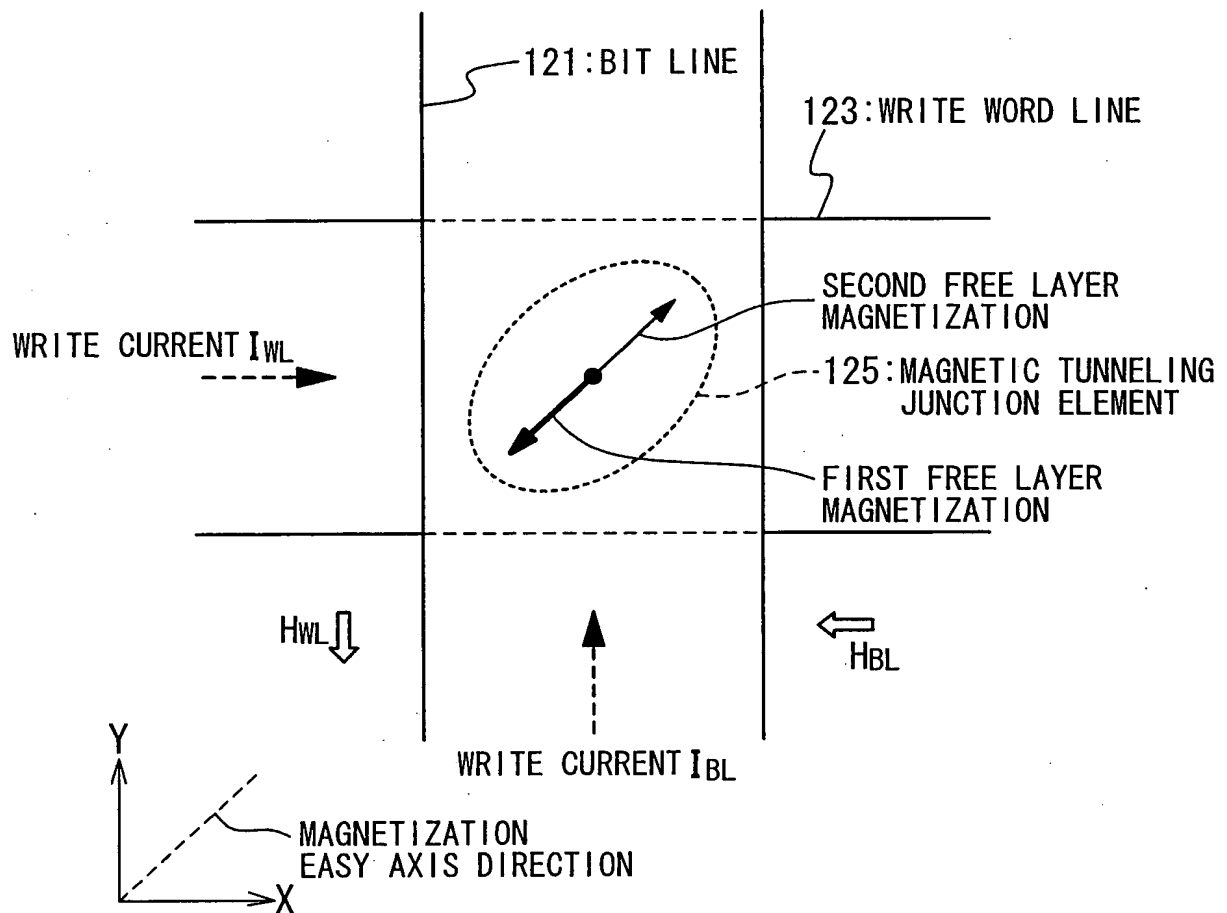


Fig. 4

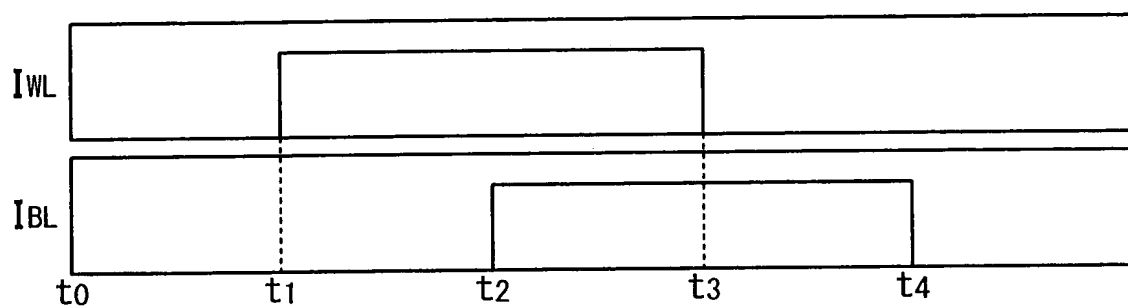


Fig. 5

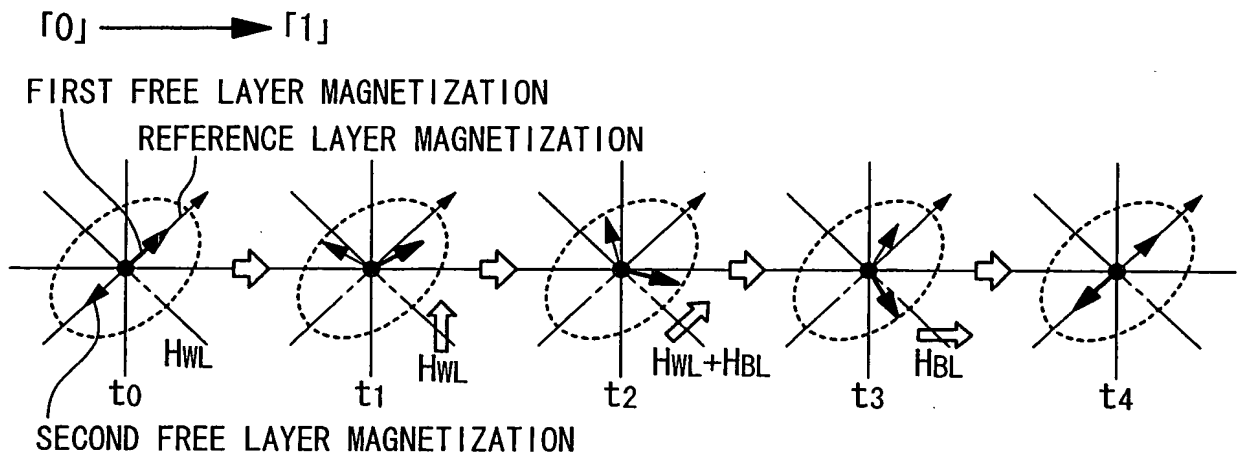


Fig. 6

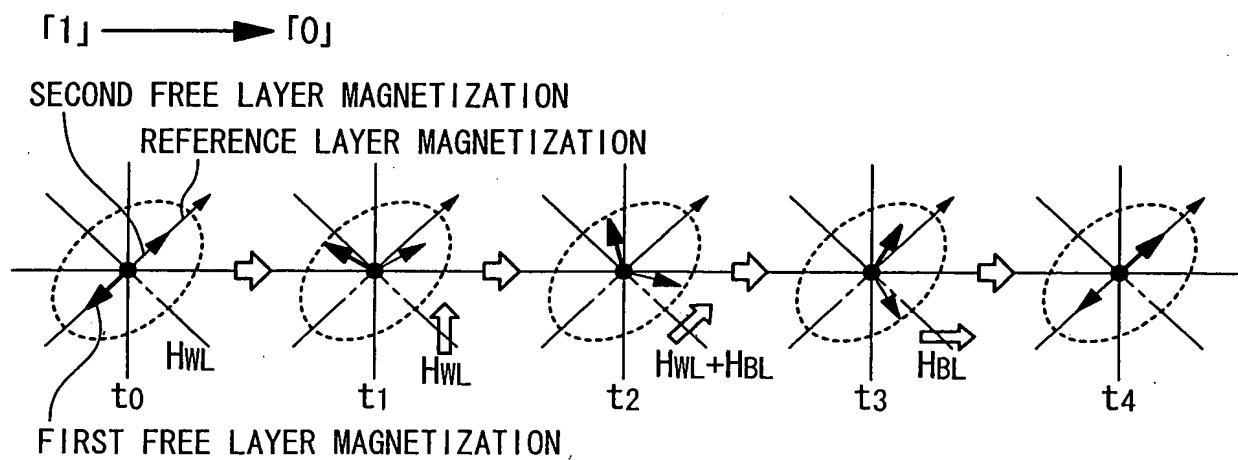


Fig. 7

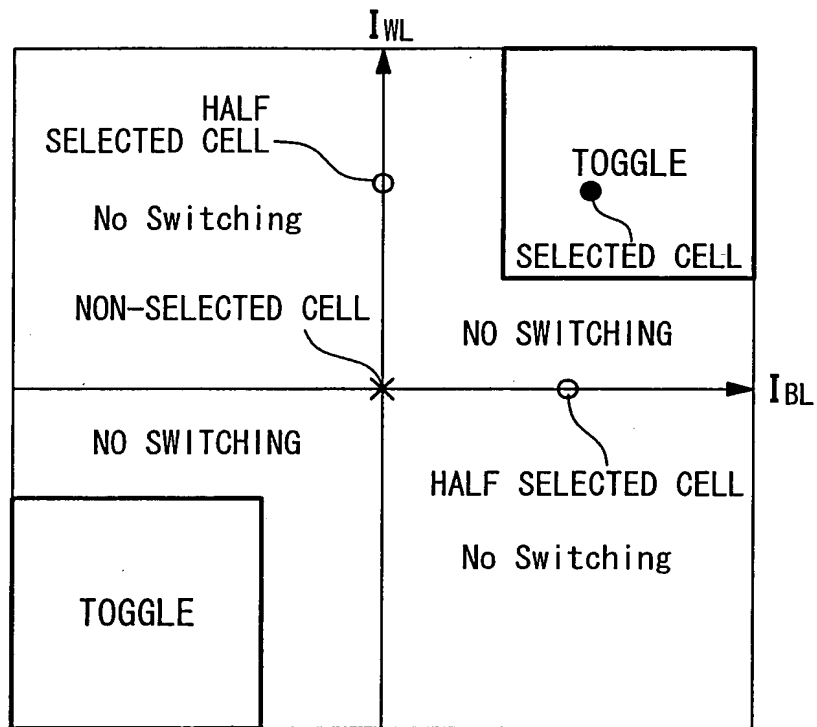


Fig. 8

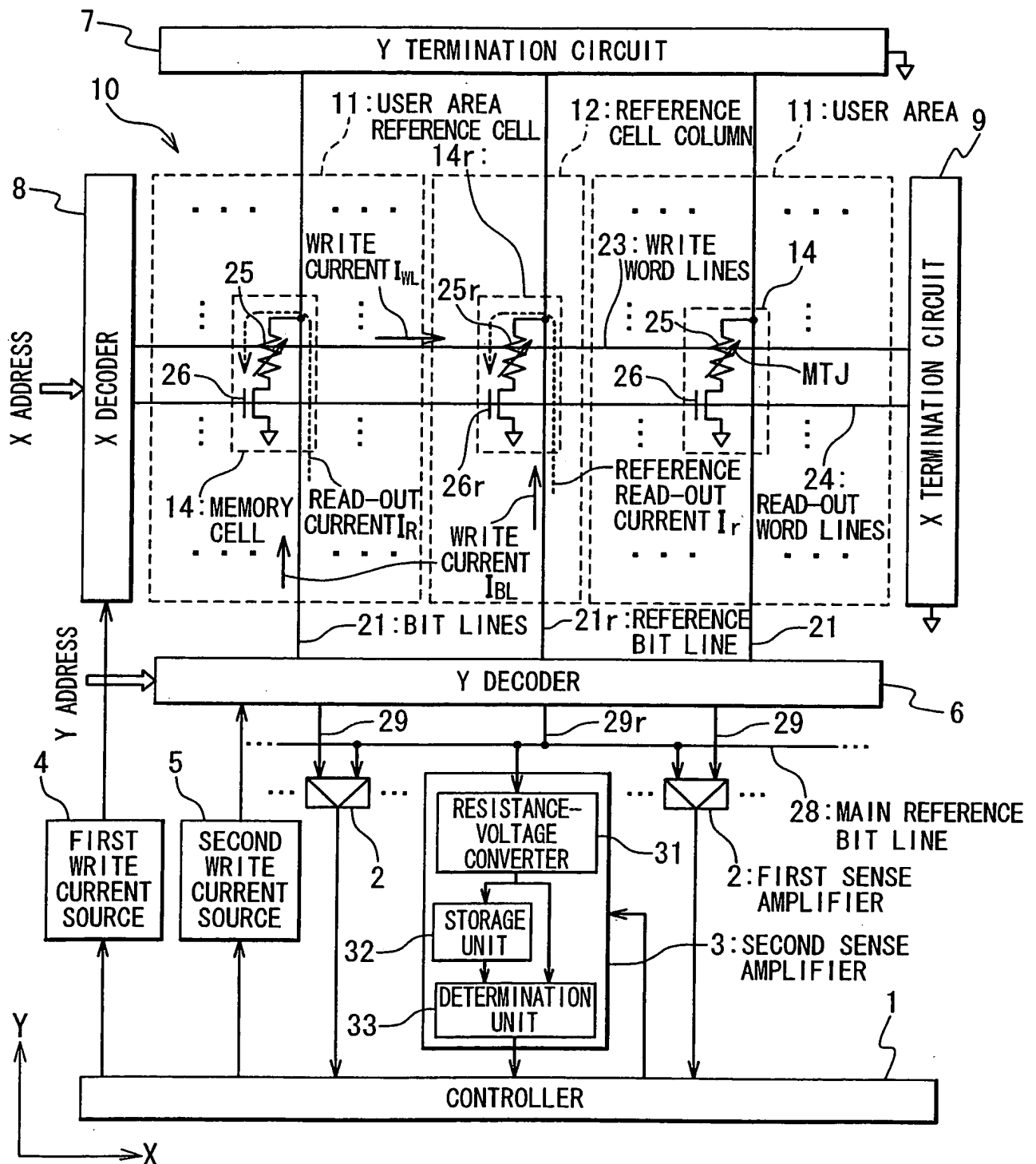
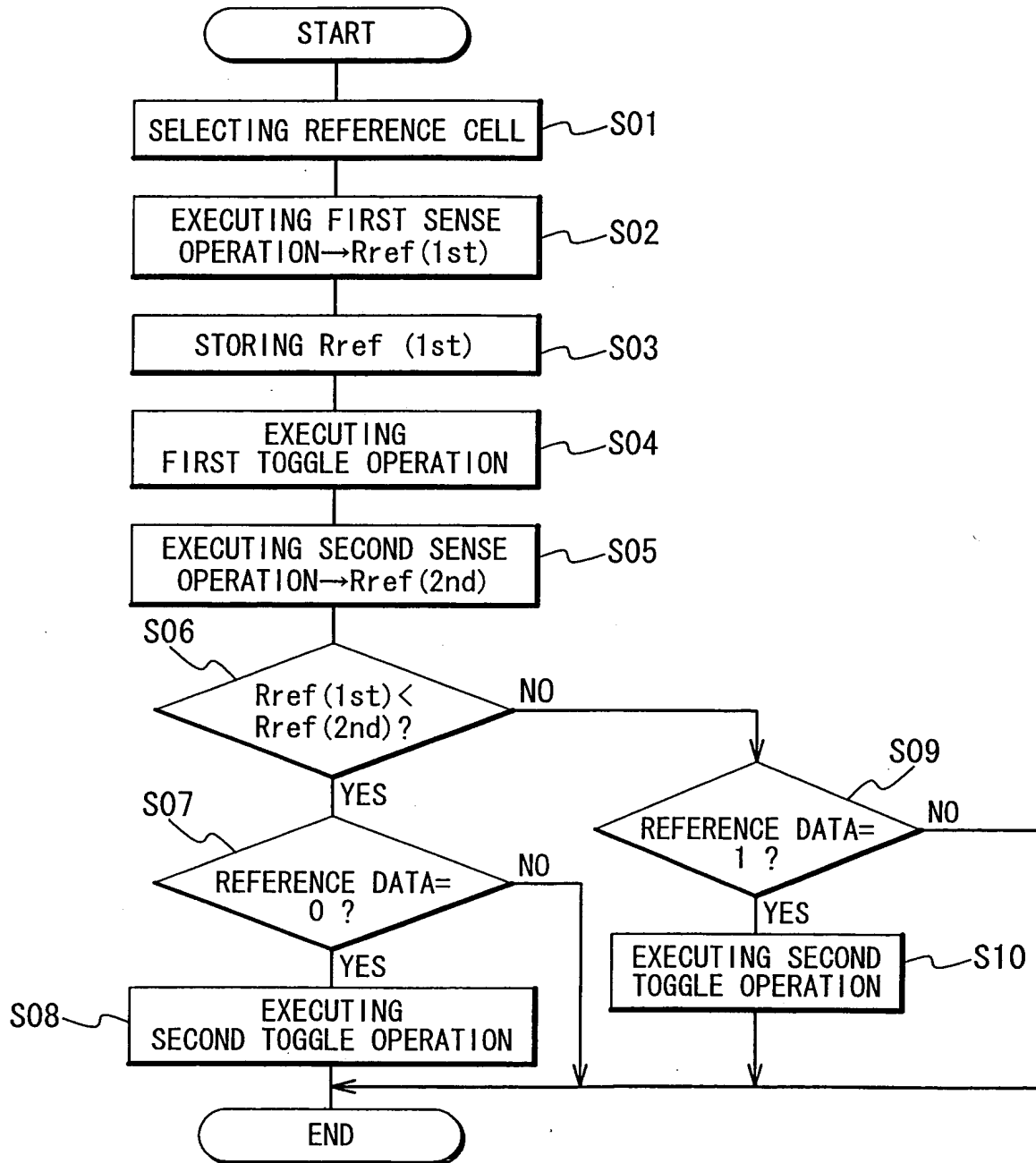


Fig. 9



3: SECOND SENSE AMPLIFIER

31: RESISTANCE-VOLTAGE CONVERTER

32: STORAGE UNIT

33: DETERMINATION UNIT

41: REFERENCE READ-OUT CURRENT

42: LOAD CAPACITOR

43: FIRST SWITCH UNIT

44: CAPACITOR

45: SECOND SWITCH UNIT

46: OPERATIONAL AMPLIFIER

47: LATCH CIRCUIT

48: EXCLUSIVE LOGICAL SUM GATE

21r: REFERENCE BIT LINE

25r: Rref

6: DIODE

14r: REFERENCE CELL

24: READ-OUT WORD LINE

28: MAIN REFERENCE BIT LINE

10: CELL ARRAY

Y DECODER

Vc

Vb

Vref

V0

Vi

φ1

φ2

φ3

DOUT

TG2EN

REFERENCE INFORMATION

Fig. 11

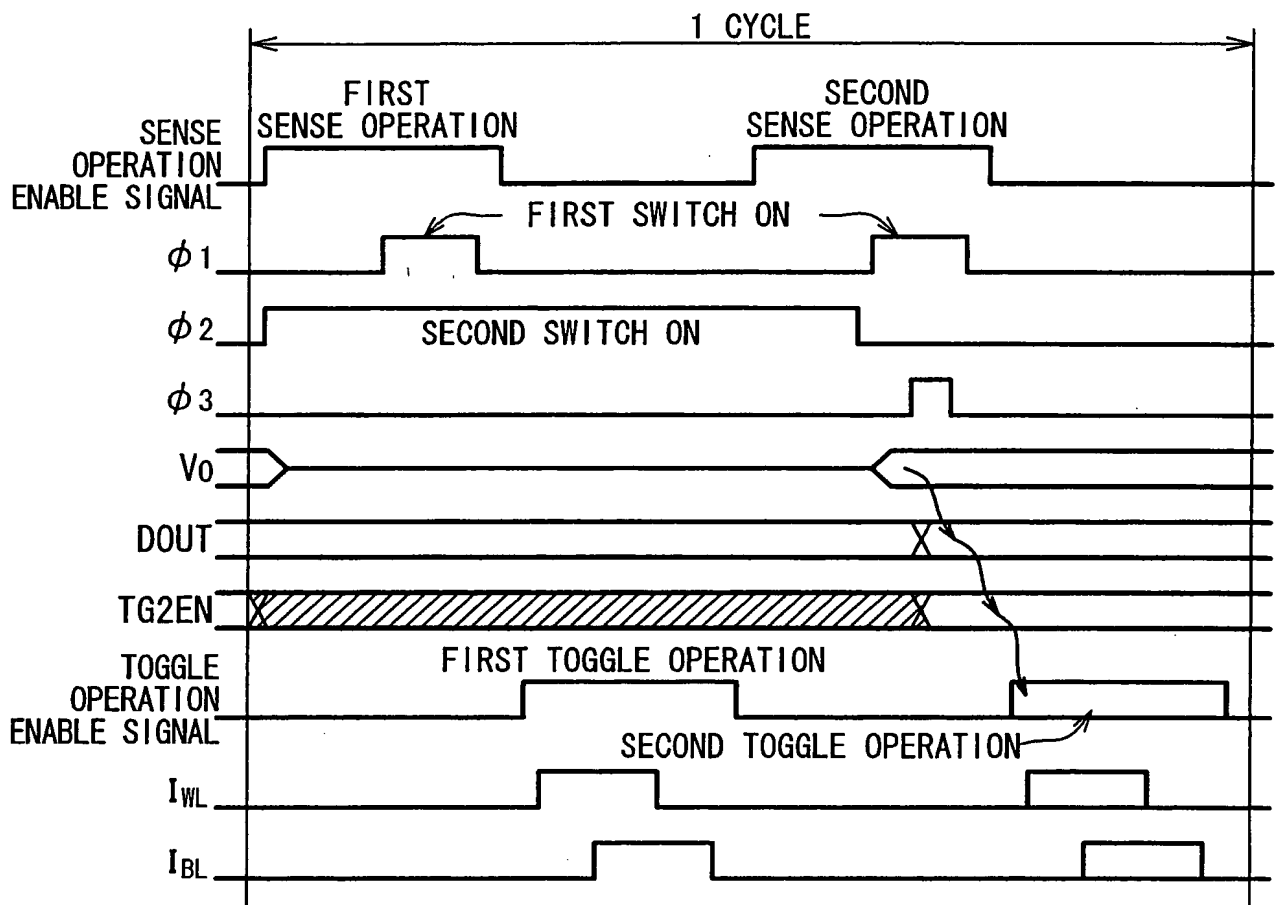


Fig. 12

DOUT="0" CASE

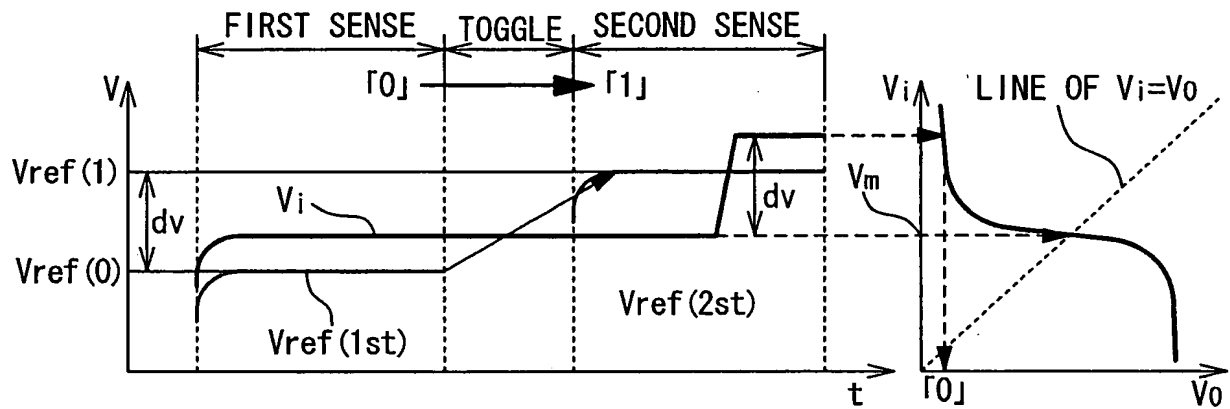


Fig. 13

DOUT="1" CASE

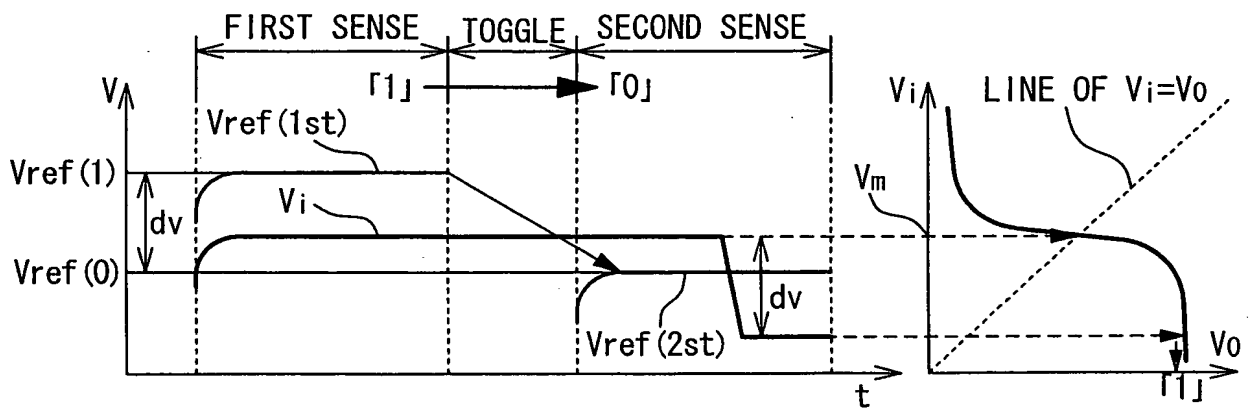


Fig. 14

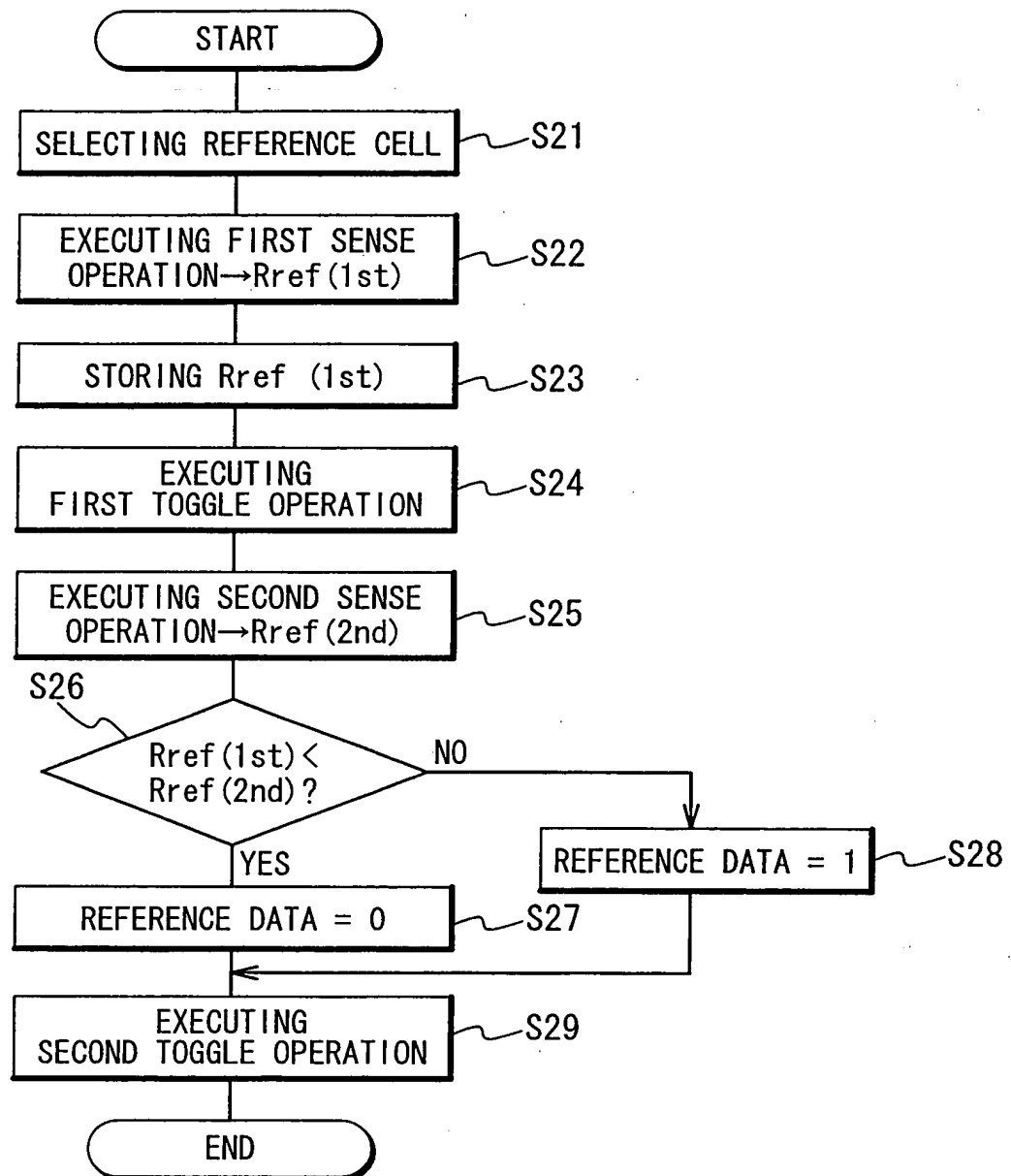


Fig. 15

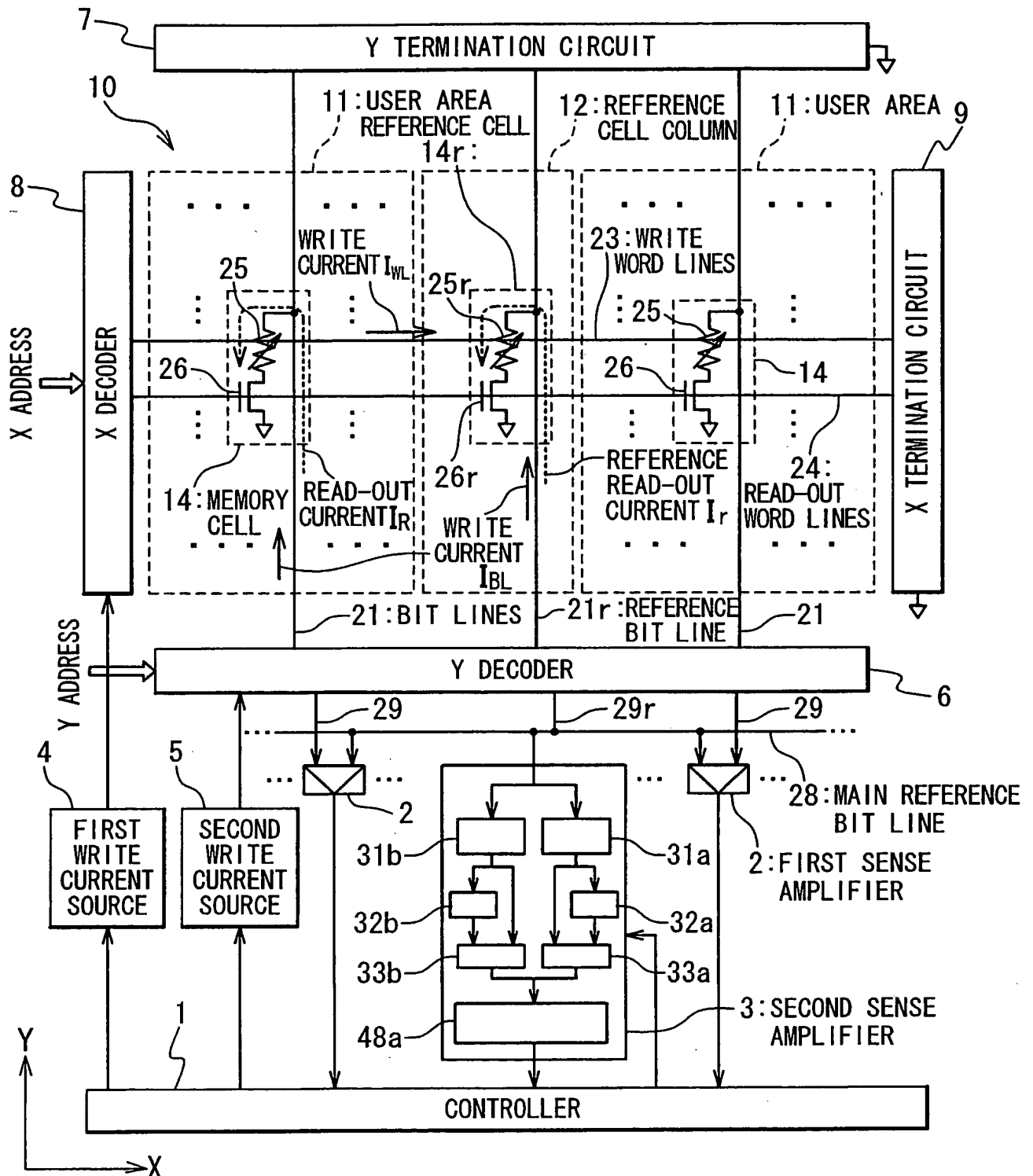


Fig. 16

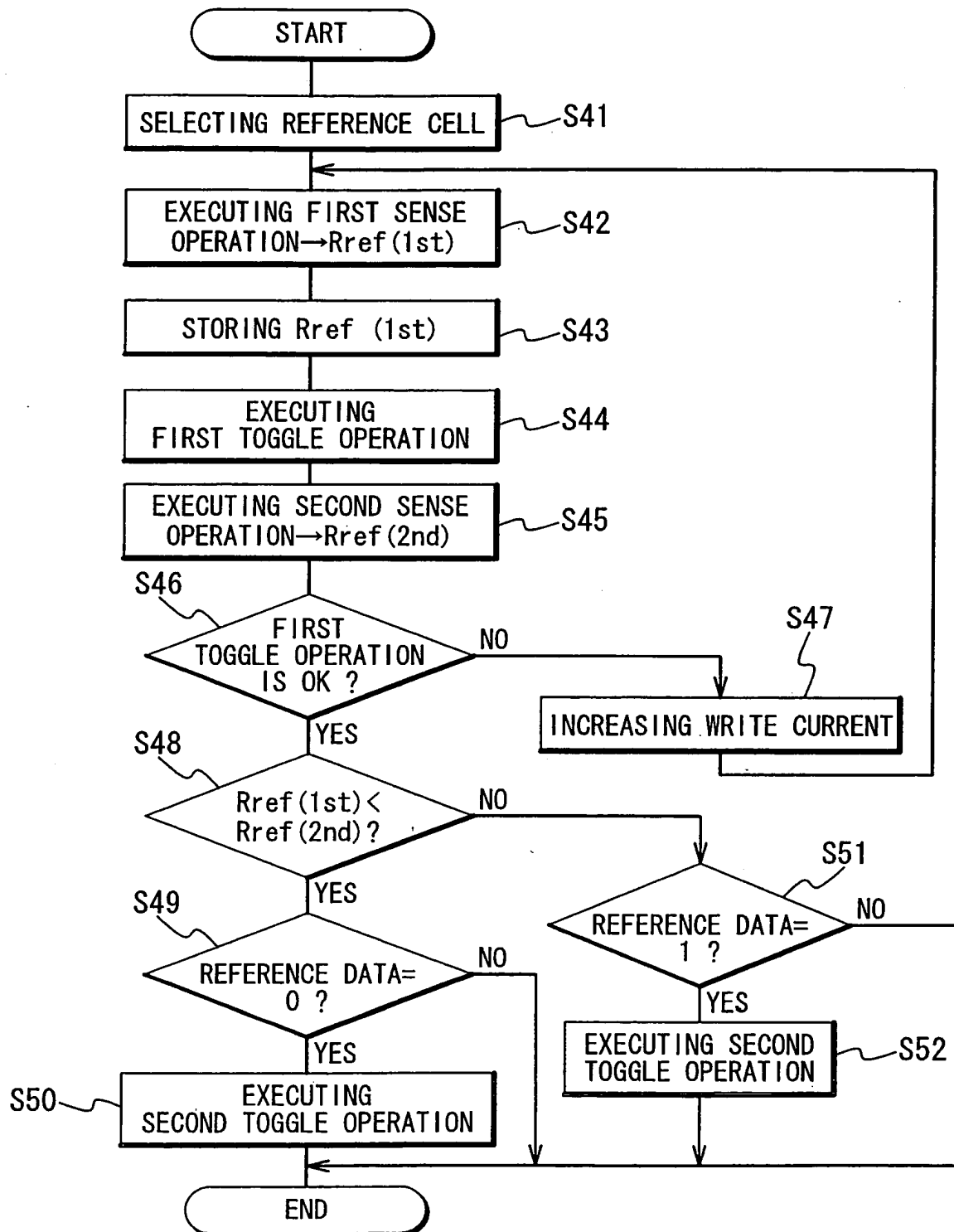


Fig. 17

The diagram illustrates a 3:1 sense amplifier circuit, labeled Fig. 17. It features two parallel processing paths for first and second determination units, connected to a central reference bit line (28) and word lines (24).

First Path (Left):

- 31a: FIRST RESISTANCE - VOLTAGE CONVERTER:** Receives V_c and V_{ref} to produce V_{off} .
- 32a: FIRST STORAGE UNIT:** A storage capacitor (41a) connected to V_{ref} and the reference bit line (28).
- 33a: FIRST DETERMINATION UNIT:** A latch circuit (47a) that receives V_{off} and the reference bit line (28) to produce $DOUT$.

Second Path (Right):

- 31b: SECOND RESISTANCE - VOLTAGE CONVERTER:** Receives V_{ref} and the reference bit line (28) to produce V_{off} .
- 32b: SECOND STORAGE UNIT:** A storage capacitor (41b) connected to V_{ref} and the reference bit line (28).
- 33b: SECOND DETERMINATION UNIT:** A latch circuit (47b) that receives V_{off} and the reference bit line (28) to produce $TG2EN$ and $TGERR$.

Reference and Control:

- 28: MAIN REFERENCE BIT LINE:** A central line providing V_{ref} to the storage units and V_{off} to the latch circuits.
- 24: READ-OUT WORD LINES:** Connected to the storage units (41a, 41b) and the reference bit line (28).
- Y DECODER:** Receives V_{ref} and the reference bit line (28) to produce V_{off} .
- 10: CELL ARRAY:** The overall structure of the sense amplifier.

F i g . 1 8

ID	REFERENCE INFORMATION	Q1	Q2	DOUT	TG2EN	TGERR
1	0	0	0	0	1	0
2	0	0	1	X	0	1
3	0	1	0	X	0	1
4	0	1	1	1	0	0
5	1	0	0	0	0	0
6	1	0	1	X	0	1
7	1	1	0	X	0	1
8	1	1	1	1	1	0

Fig. 19

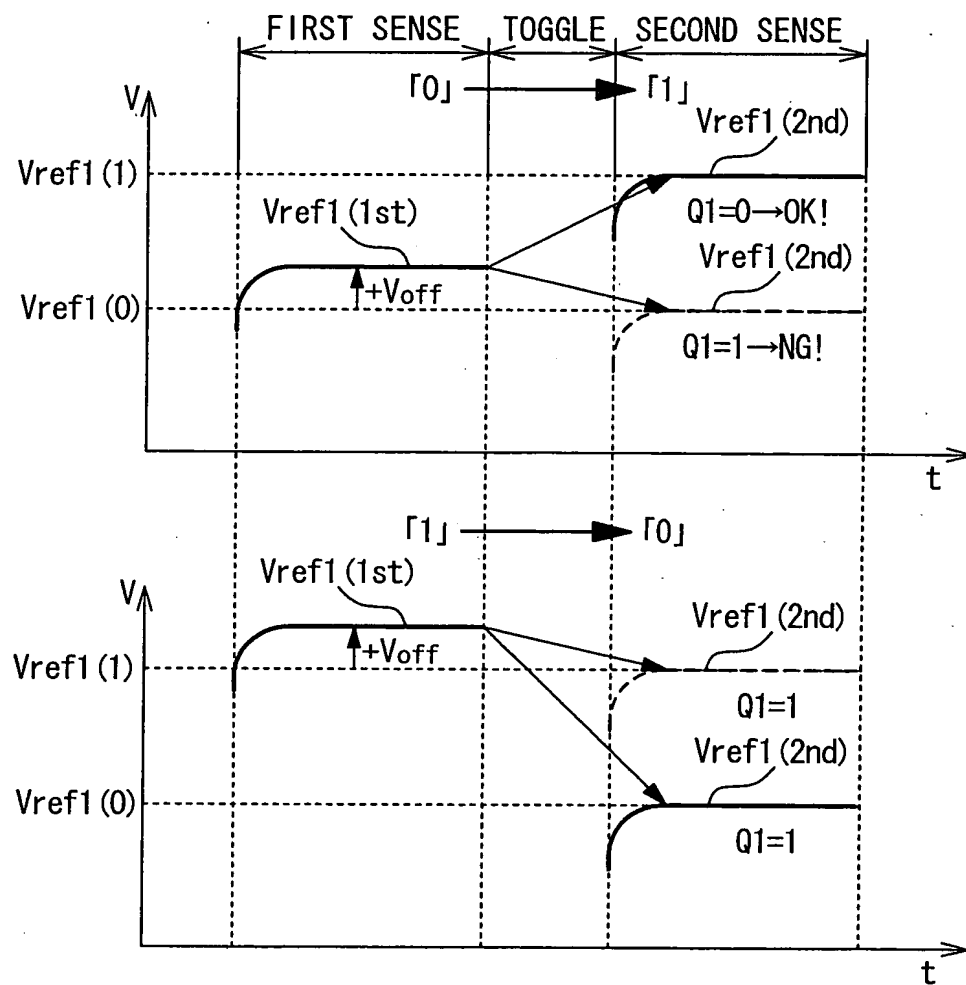


Fig. 20

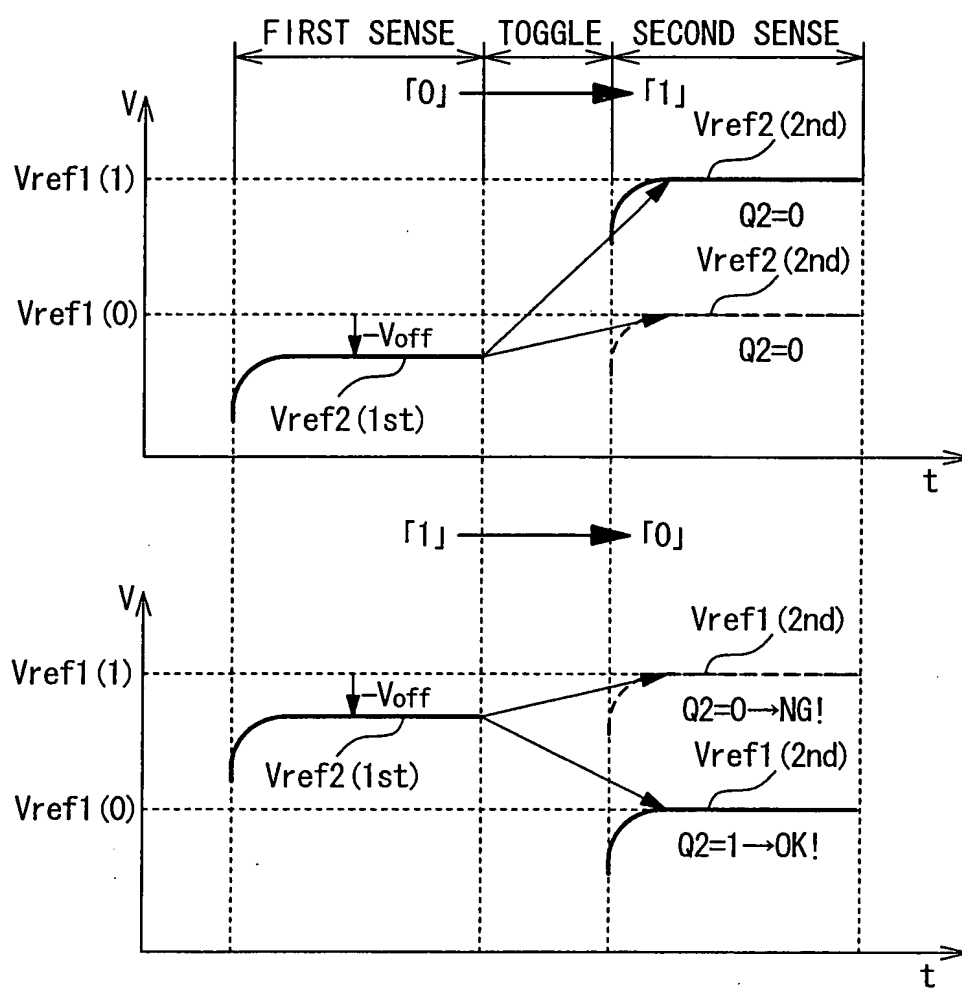


Fig. 21

